

1.Description

The IRLML0100TR uses advanced trench technology to provide excellent $R_{DS(on)}$ with low gate charge. This device is suitable for use as a loads witch or in PWM applications.

3.Benefits

- Multi-vendor compatibility
- Easier manufacturing

2.Features

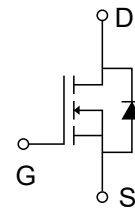
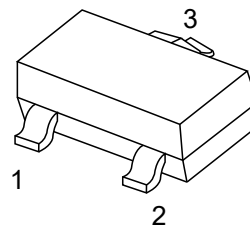
- $V_{DS(V)}=100V$
- $R_{DS(on)}<220m\Omega(V_{GS}=10V)$
- $R_{DS(on)}<235m\Omega(V_{GS}=4.5V)$

- Environmentally friendly
- Increased reliability

4.Pinning information

Pin	Symbol	Description
1	G	GATE
2	S	SOURCE
3	D	DRAIN

SOT-23



5.Maximum ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter		Symbol	Value	Units
Drain-Source Voltage		V_{DS}	100	V
Continuous Drain Current, V_{GS} @ 10V	$T_A=25^{\circ}C$	I_D	1.6	A
Continuous Drain Current, V_{GS} @ 10V	$T_A=70^{\circ}C$		1.3	
Pulsed Drain Current		I_{DM}	7	
Maximum Power Dissipation	$T_A=25^{\circ}C$	P_D	1.3	W
Maximum Power Dissipation	$T_A=70^{\circ}C$		0.8	
Linear Derating Factor			0.01	W/ $^{\circ}C$
Gate-to-Source Voltage		V_{GS}	± 16	V
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^{\circ}C$



6. Thermal resistance rating

Parameter	Symbol	Typ	Max	Units
Junction-to-Ambient ③	$R_{\theta JA}$		100	°C/W
Junction-to-Ambient ($t < 10s$) ④	$R_{\theta JA}$		99	°C/W

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ③ Surface mounted on 1 in square Cu board.



7. Electrical Characteristics $T_J=25^{\circ}\text{C}$

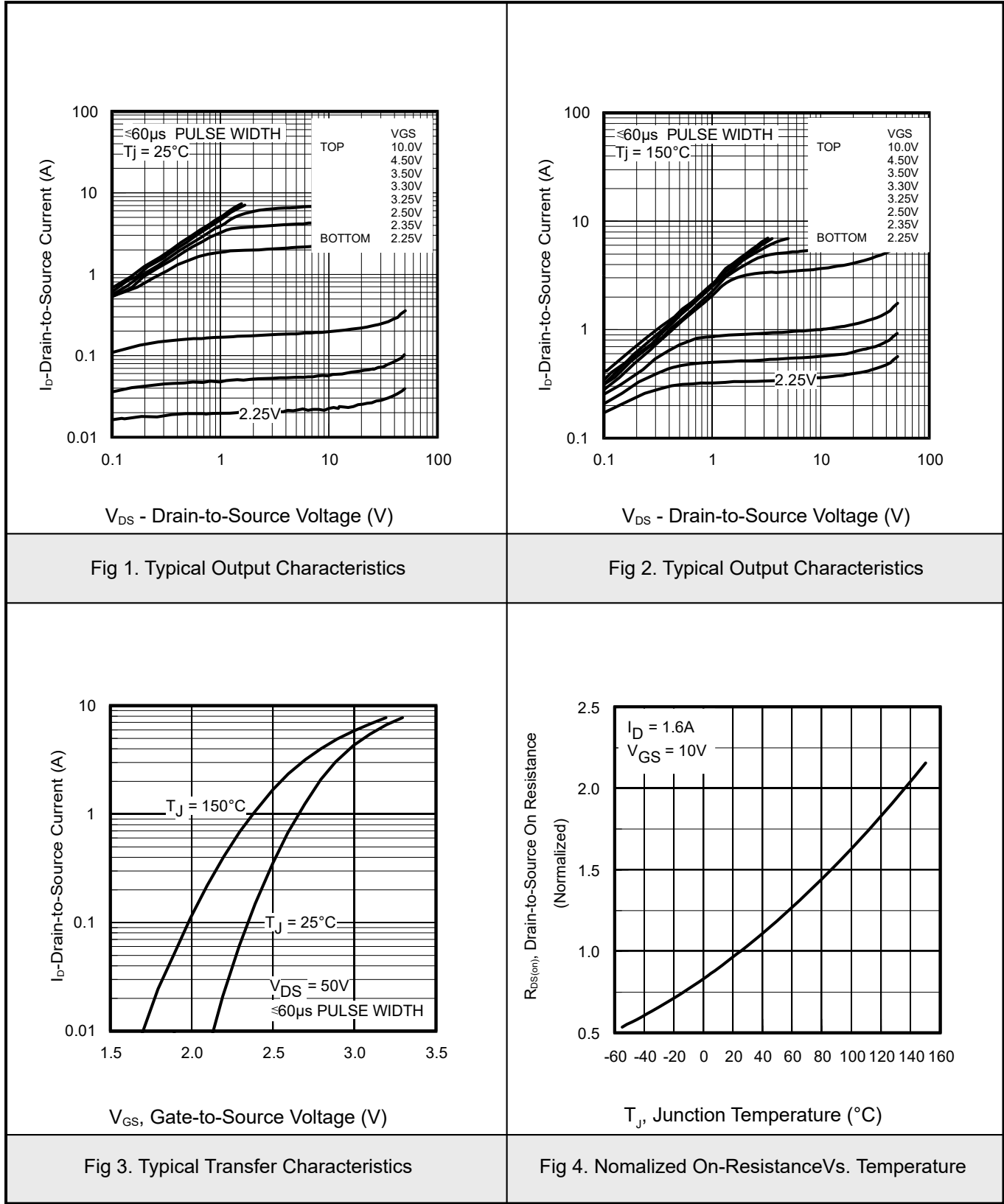
Parameter	Symbol	Conditions	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	100			V
Breakdown Voltage Temp. Coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	$I_D=1\text{mA}$, Reference to 25°C		0.1		$\text{V}/^{\circ}\text{C}$
Static Drain-to-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=4.5\text{V}$, $I_D=1.3\text{A}$ ②		190	235	$\text{m}\Omega$
		$V_{GS}=10\text{V}$, $I_D=1.6\text{A}$ ②		178	220	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=25\mu\text{A}$	1		2.5	V
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS}=100\text{V}$, $V_{GS}=0\text{V}$			20	μA
		$V_{DS}=100\text{V}$, $V_{GS}=0\text{V}$, $T_J=125^{\circ}\text{C}$			250	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS}=16\text{V}$			100	nA
Gate-to-Source Reverse Leakage		$V_{GS}=-16\text{V}$			-100	
Internal Gate Resistance	R_G			1.3		Ω
Forward Transconductance	g_{fs}	$V_{DS}=50\text{V}$, $I_D=1.6\text{A}$	5.7			S
Total Gate Charge	Q_g	$V_{DS}=50\text{V}$		2.5		nC
Gate-to-Source Charge	Q_{gs}	$V_{GS}=4.5\text{V}$ ②		0.5		
Gate-to-Drain ("Miller") Charge	Q_{gd}	$I_D=1.6\text{A}$		1.2		
Turn-On Delay Time	$t_{D(on)}$	$V_{DD}=50\text{V}$ ②		2.2		ns
Rise Time	t_r	$I_D=1\text{A}$		2.1		
Turn-Off Delay Time	$t_{D(off)}$	$R_G=6.8\Omega$		9		
Fall Time	t_f	$V_{GS}=4.5\text{V}$		3.6		
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}$		290		pF
Output Capacitance	C_{oss}	$V_{DS}=25\text{V}$		27		
Reverse Transfer Capacitance	C_{rss}	$f=1\text{MHz}$		13		



Source-Drain Ratings and Characteristics						
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode.			1.1	A
Pulsed Source Current (Body Diode) ①	I_{SM}				7	
Diode Forward Voltage	V_{SD}	$T_J=25^{\circ}C, I_S=1.1A, V_{GS}=0V$ ②			1.3	V
Reverse Recovery Time	t_{rr}	$T_J=25^{\circ}C, V_R=50V, I_F=1.1A$		20	30	ns
Reverse Recovery Charge	Q_{rr}	$di/dt=100A/\mu s$ ②		13	20	nC

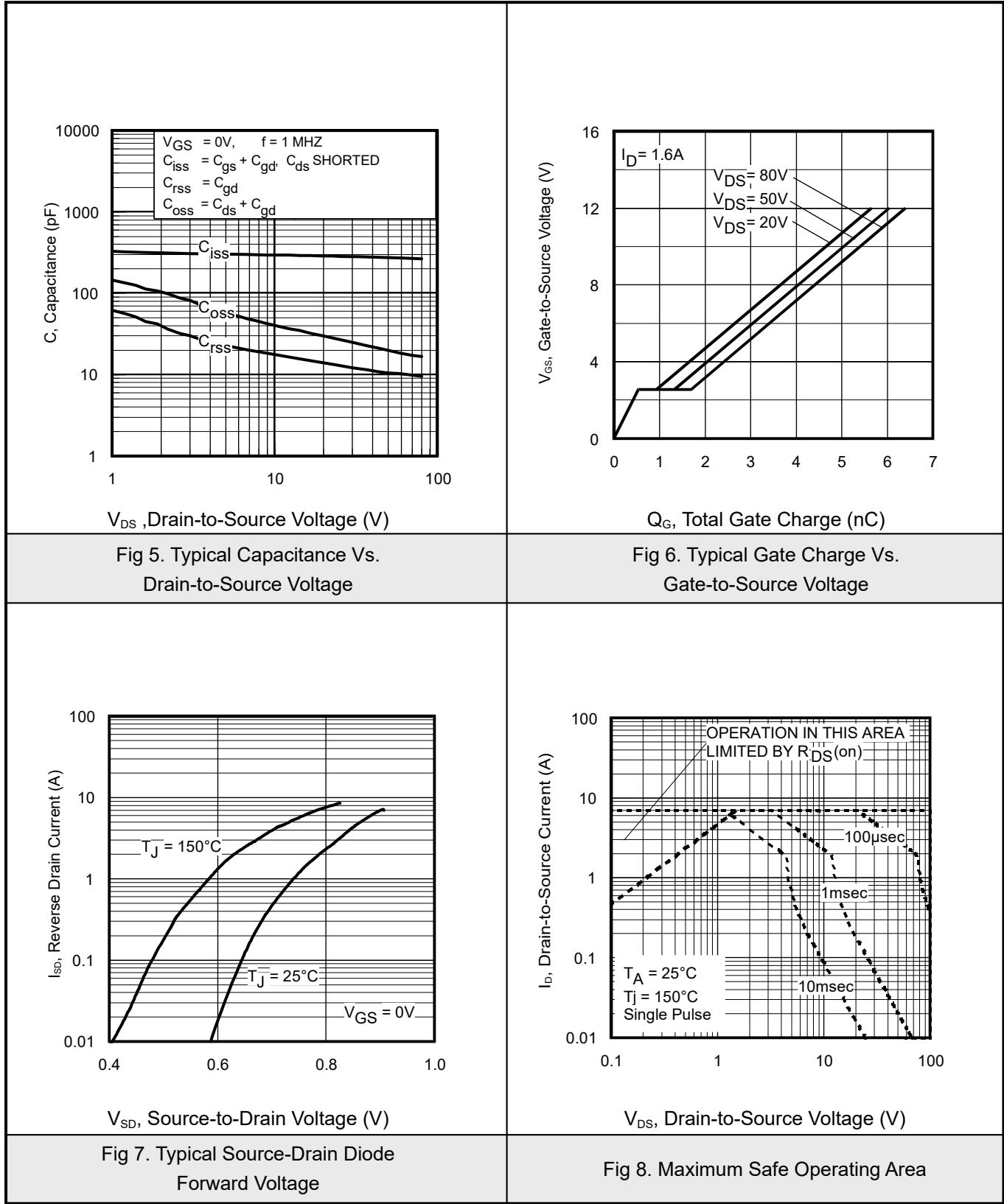


8.1Typical Characterisitics



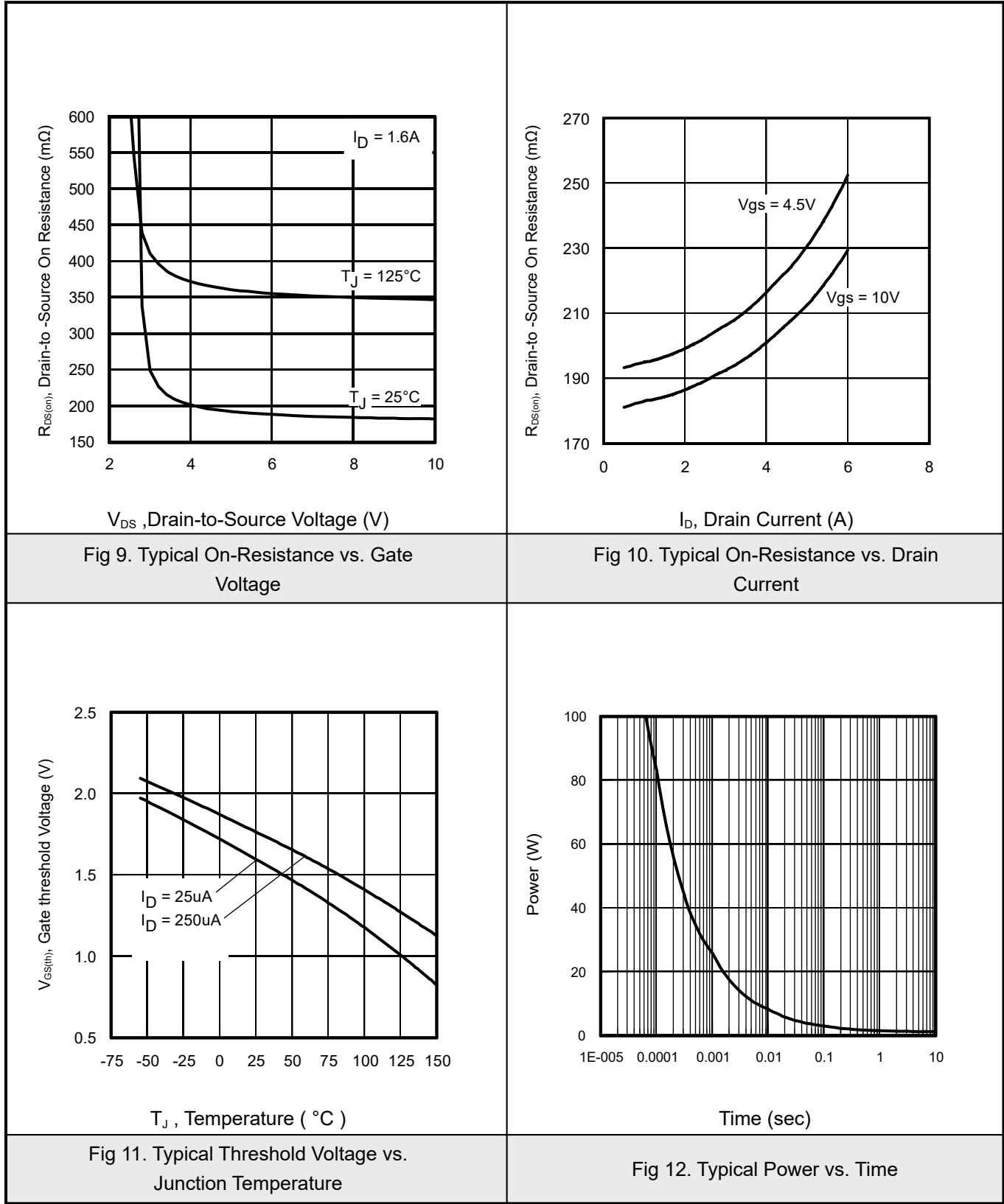


8.2Typical Characteristics





8.3Typical Characterisitics





8.4Typical Characterisitics

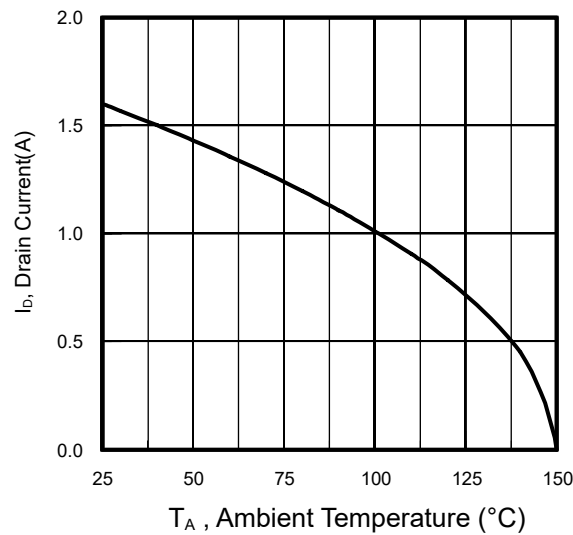


Fig 13. Maximum Drain Current vs. Ambient Temperature

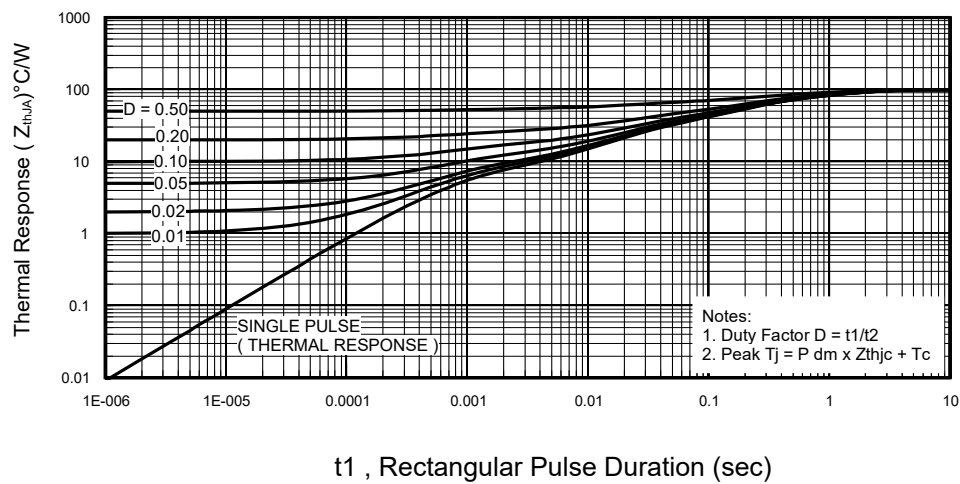


Fig 14. Typical Effective Transient Thermal Impedance, Junction-to-Ambient



8.5 Typical Characteristics

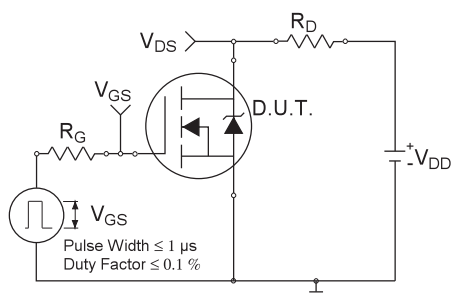


Fig 15a. Switching Time Test Circuit

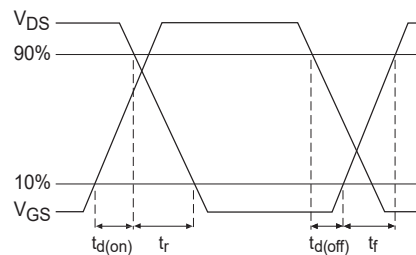


Fig 15b. Switching Time Waveforms

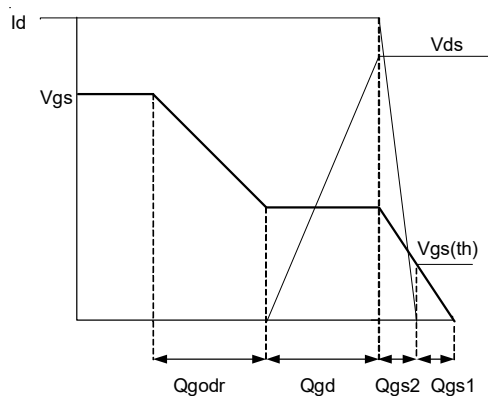


Fig 16a. Basic Gate Charge Waveform

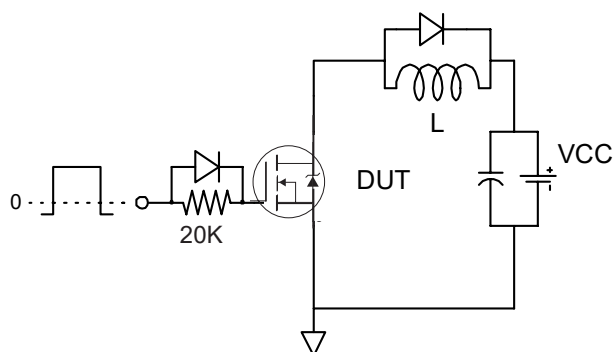
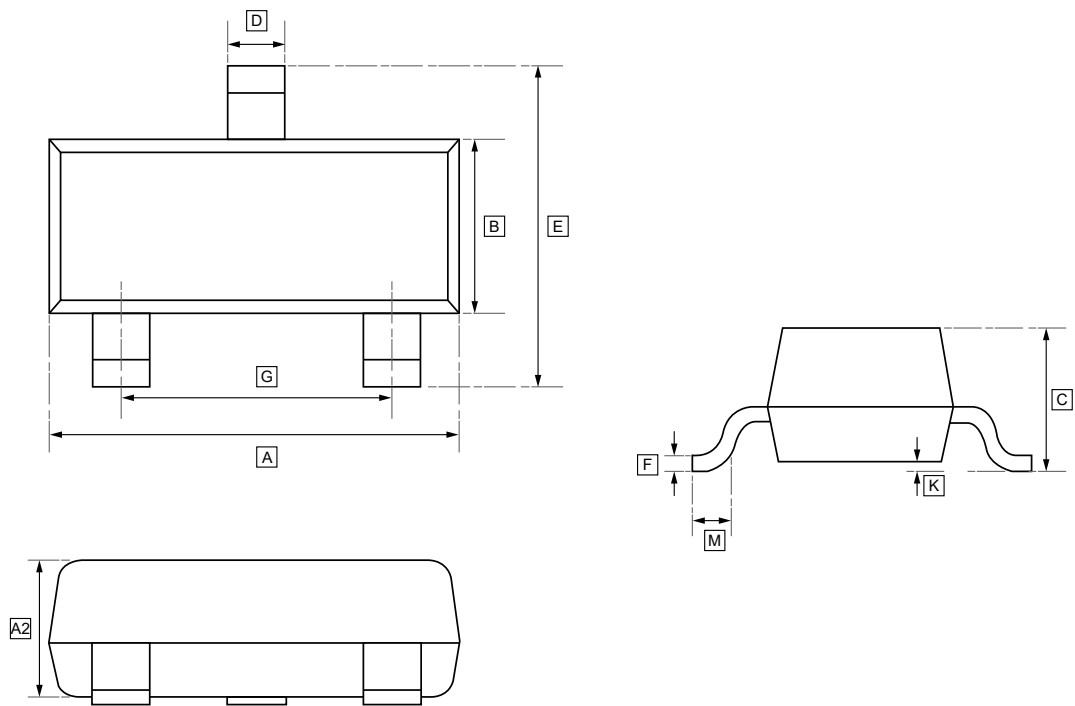


Fig 16b. Gate Charge Test Circuit



9.SOT-23 Package Outline Dimensions

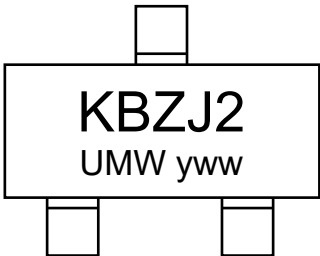


DIMENSIONS (mm are the original dimensions)

Symbol	A	B	C	D	E	G	K	M	A2	F
Min	2.85	1.20	0.90	0.40	2.25	1.80	0.00	0.30	0.95	0.095
Max	3.04	1.40	1.10	0.50	2.55	2.00	0.10	-	1.05	0.115



10.Ordering information



yww: Batch Code

Order Code	Package	Base QTY	Delivery Mode
UMW IRLML0100TR	SOT-23	3000	Tape and reel



11.Disclaimer

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